

FIG. 1

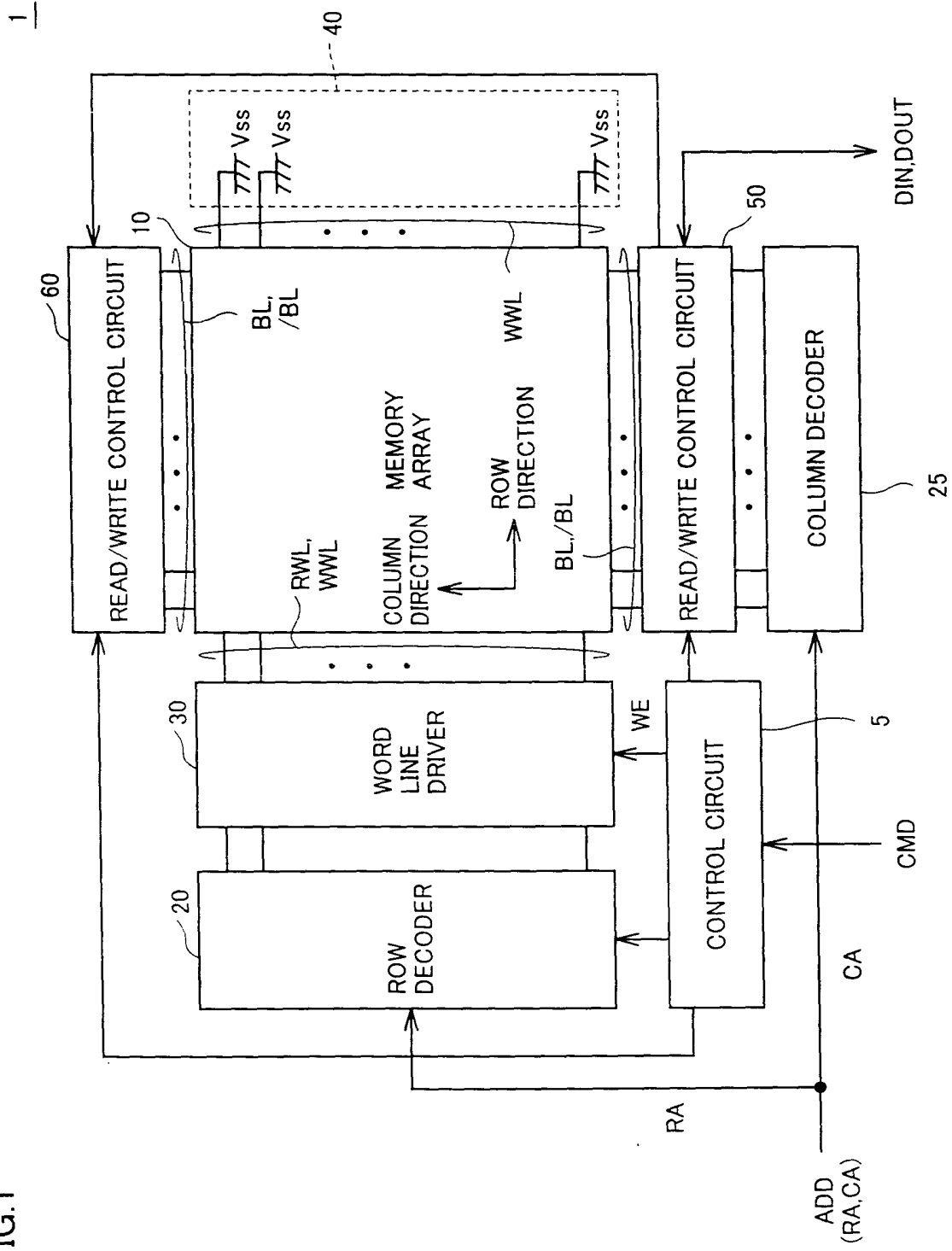


FIG.2

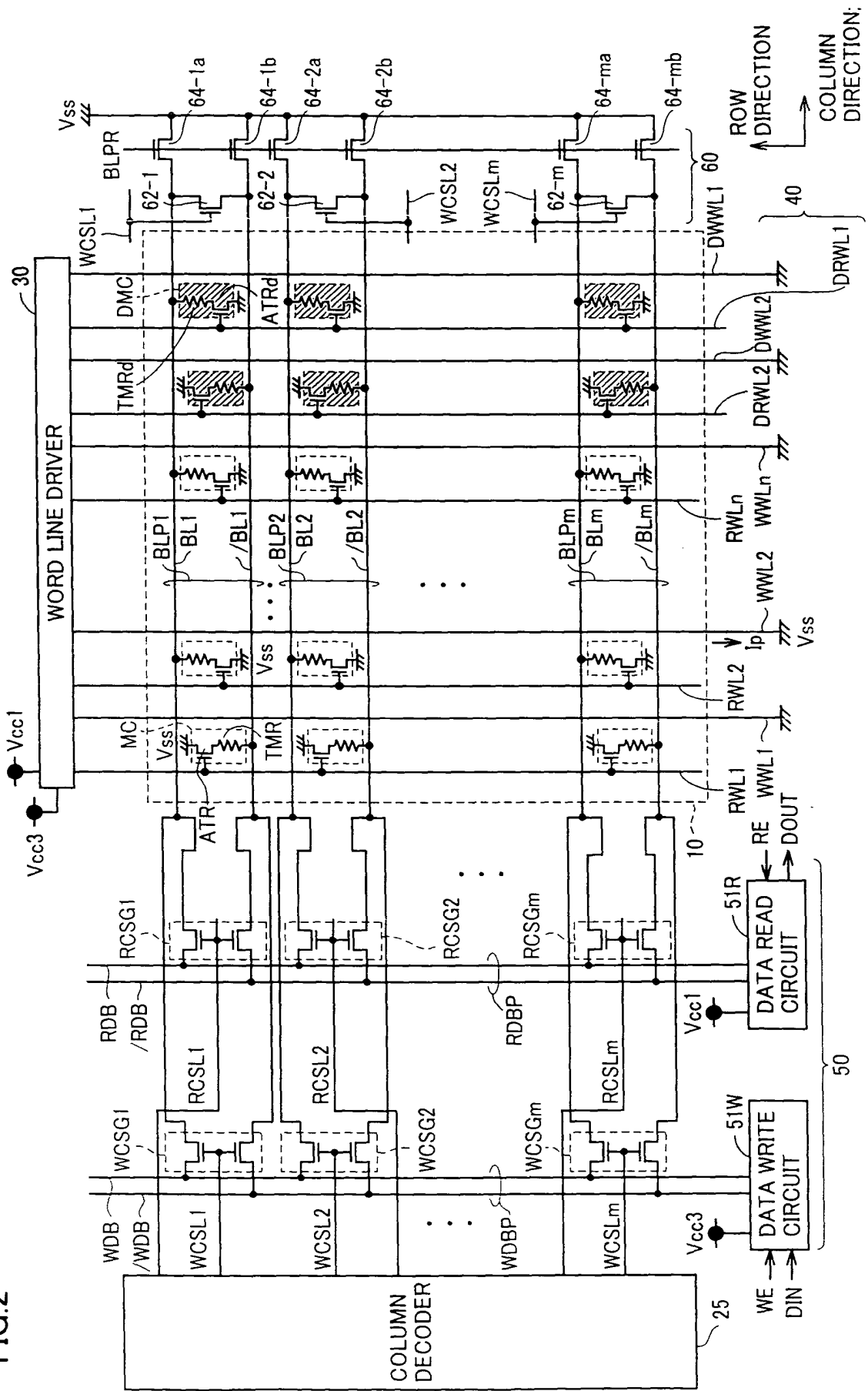


FIG.3

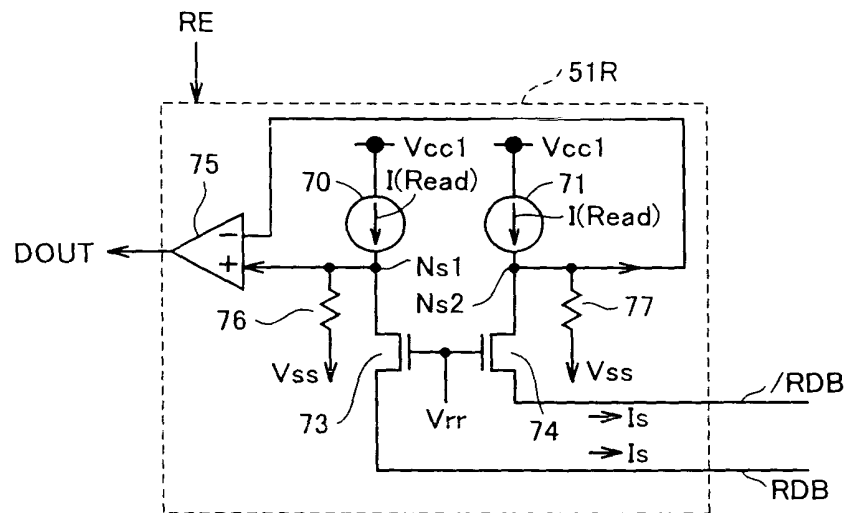


FIG. 4

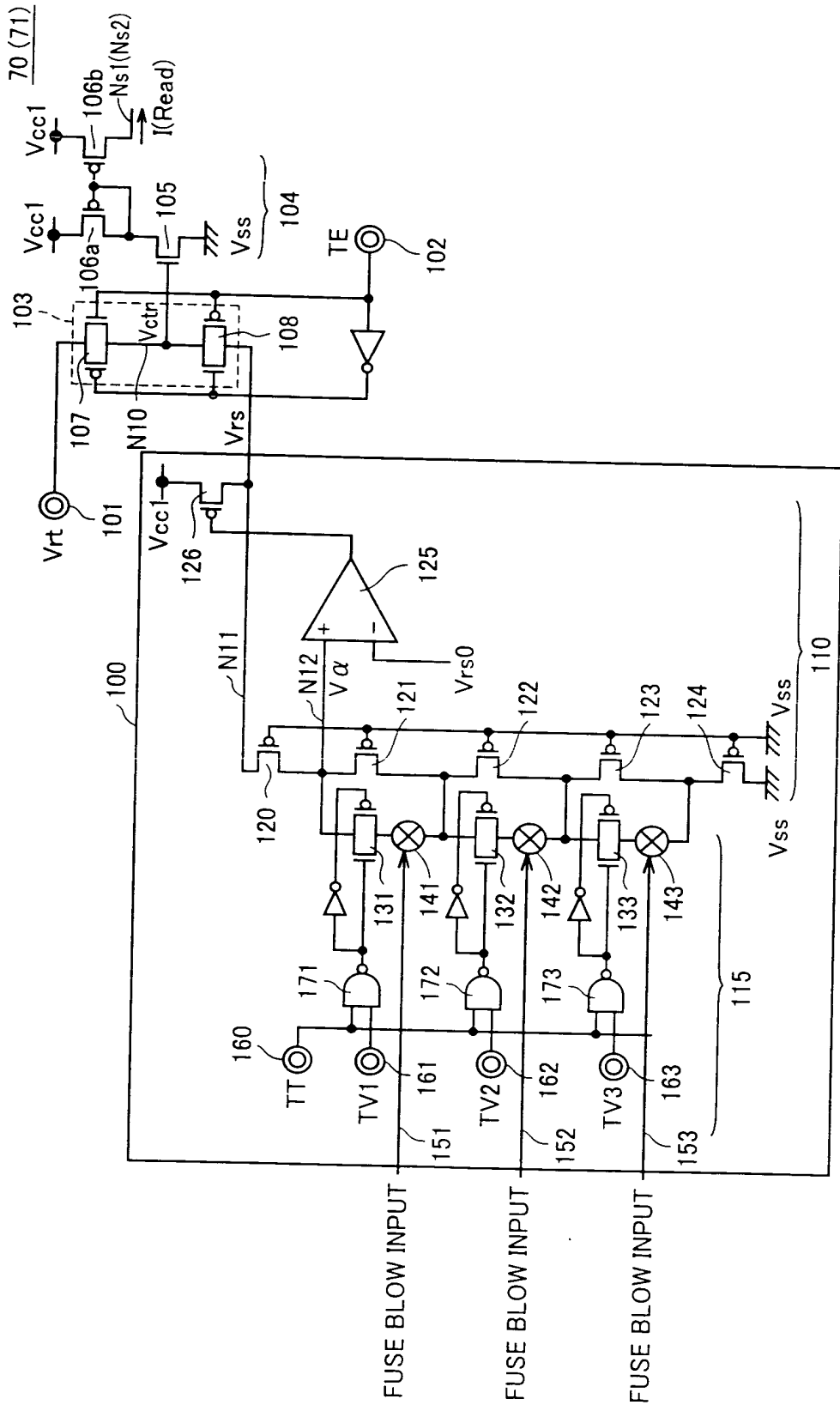


FIG.5

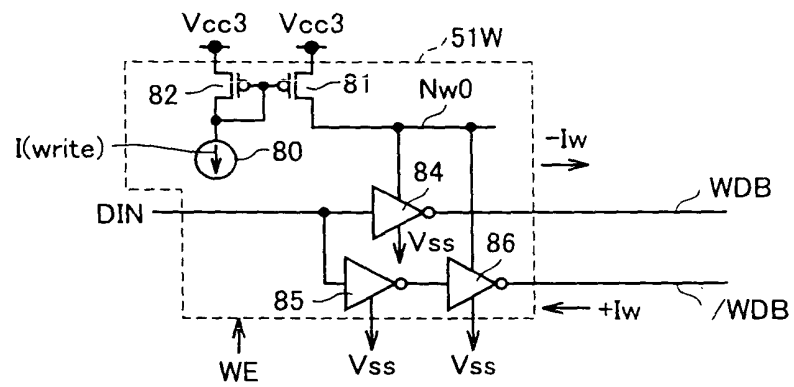


FIG.6

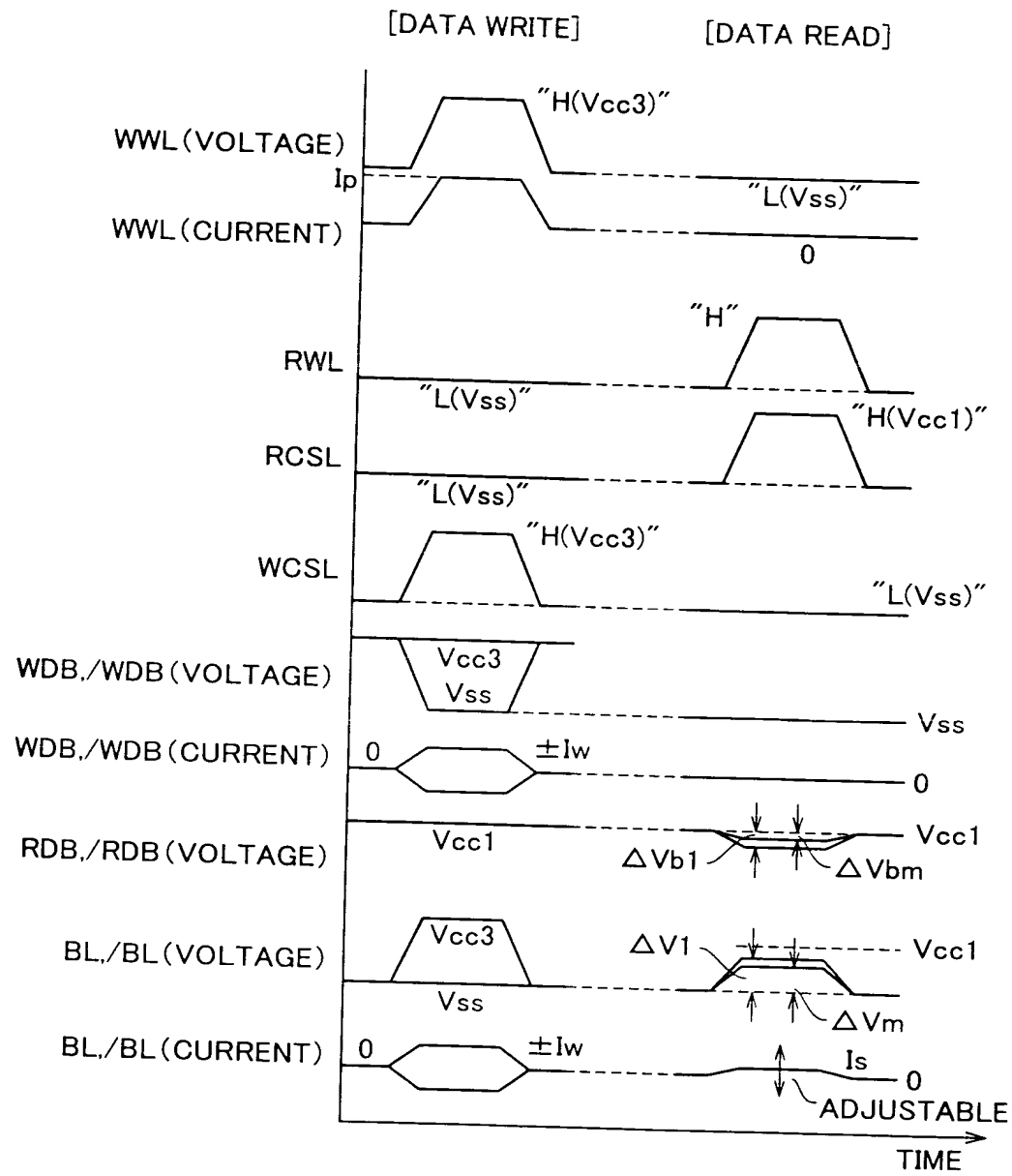


FIG.7

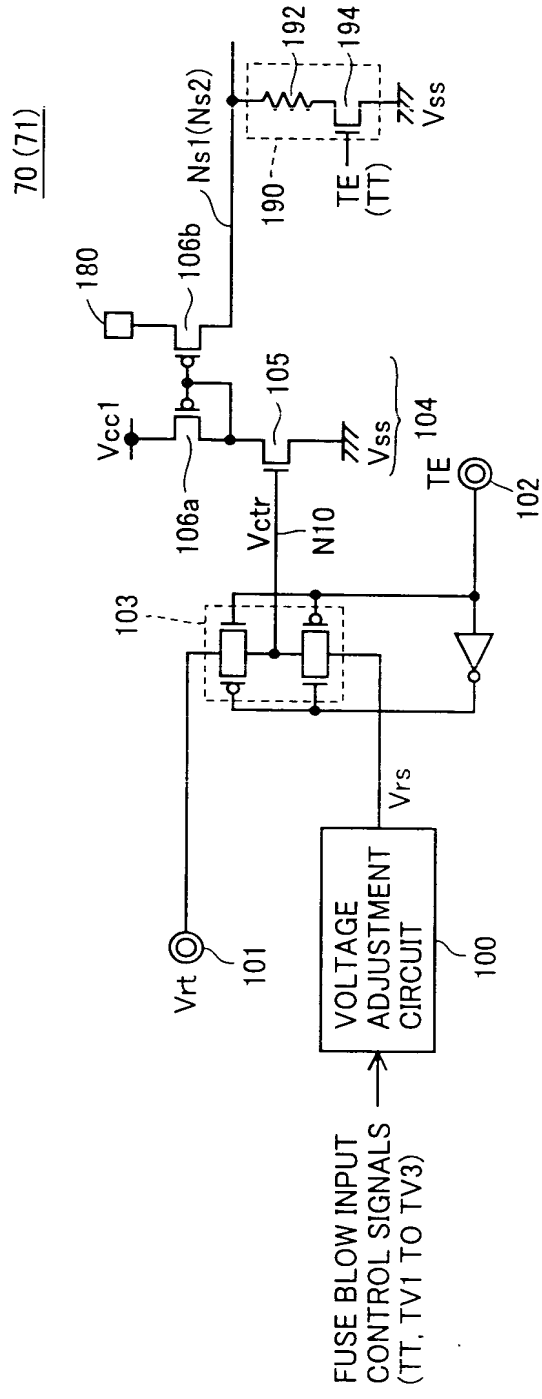


FIG.8

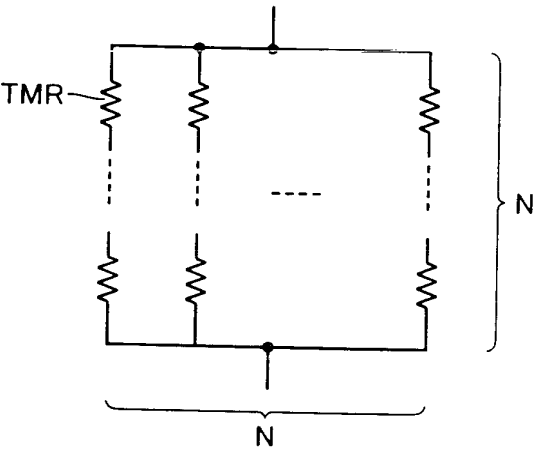


FIG.9

70 (71)

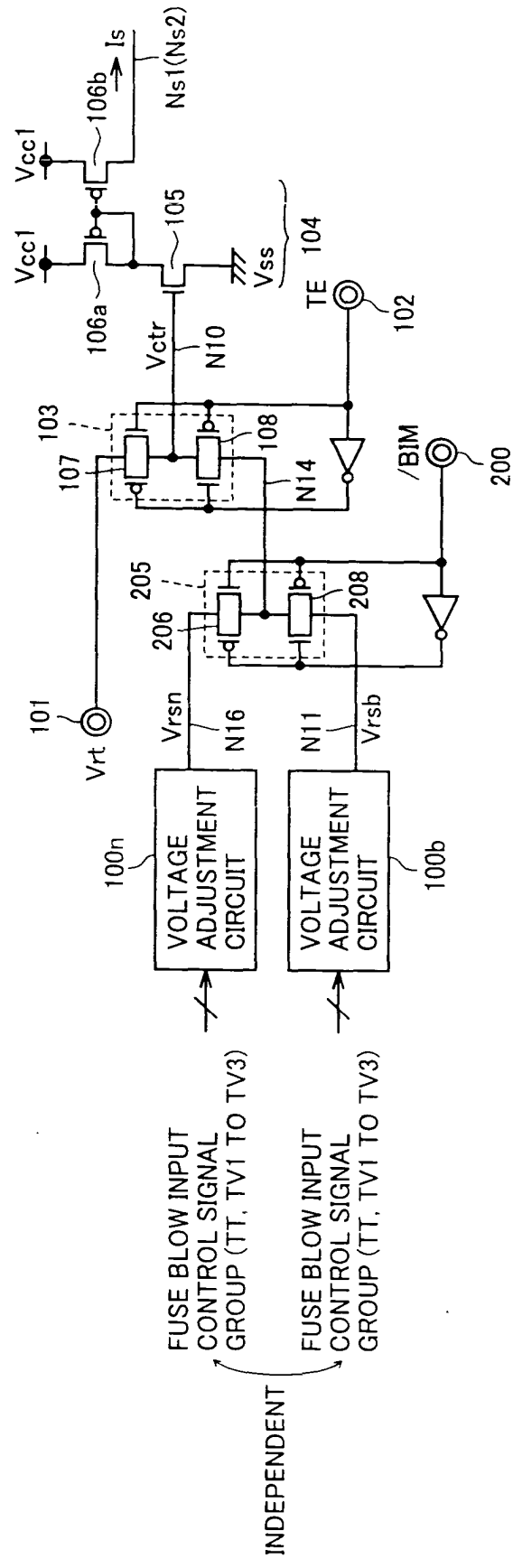


FIG.10

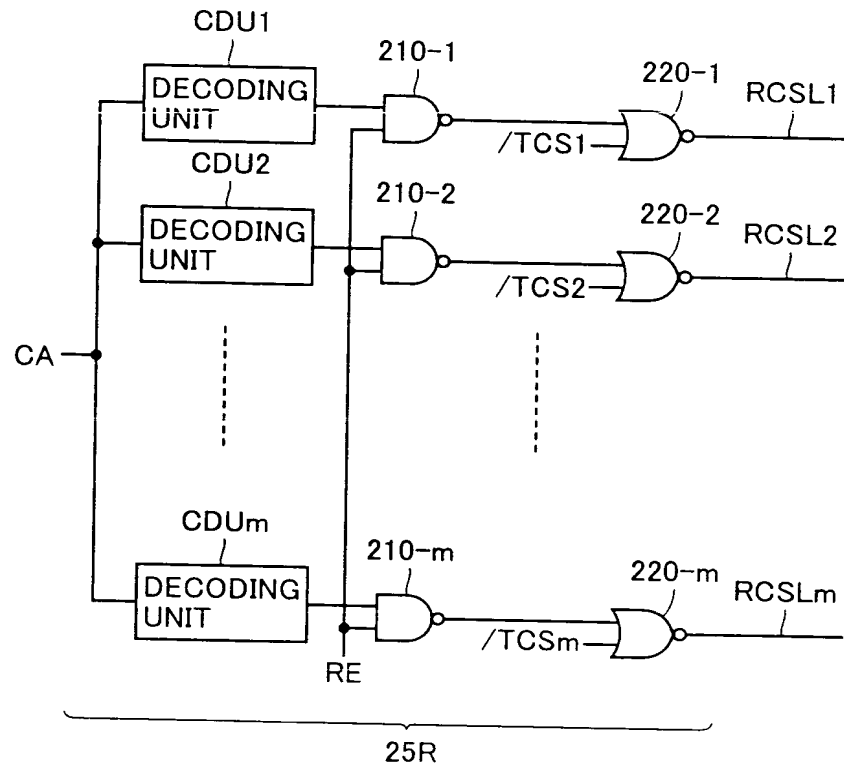


FIG.11

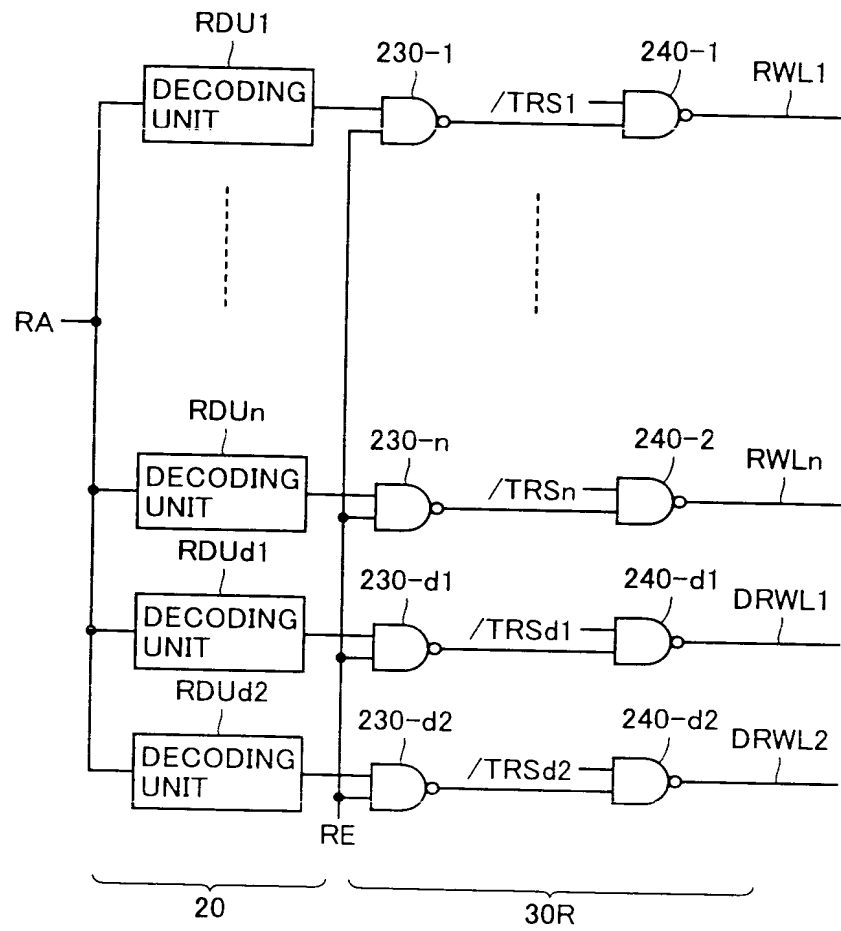


FIG.12

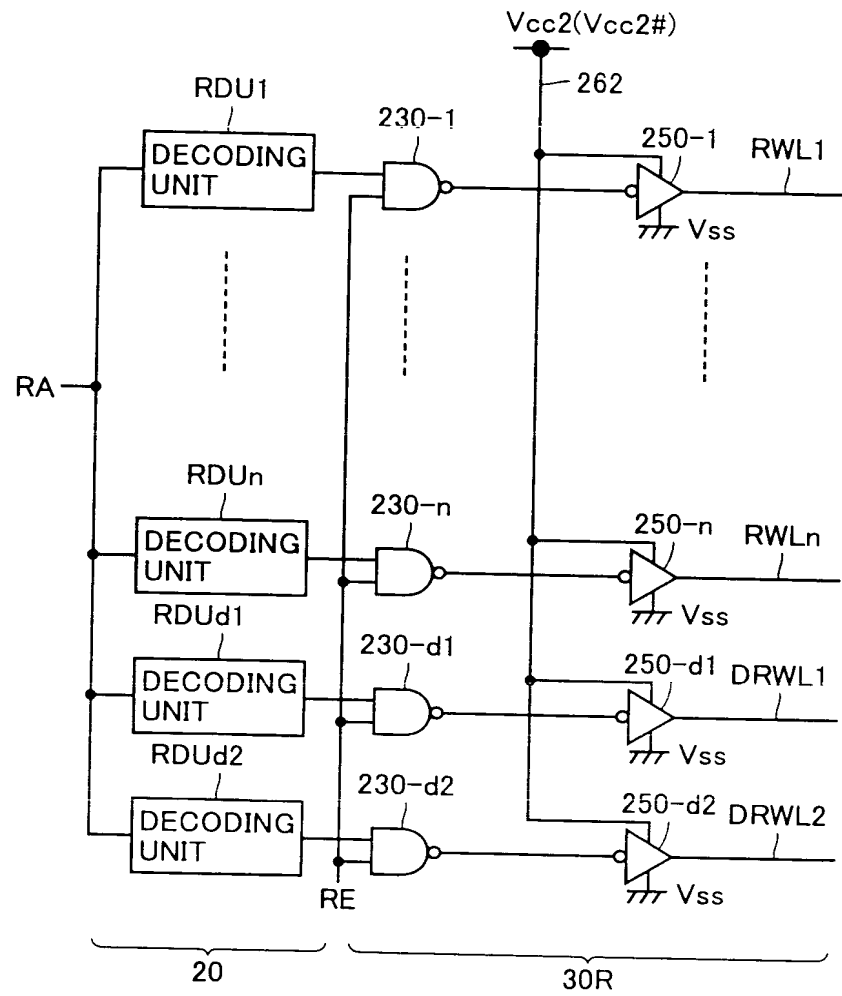


FIG. 13

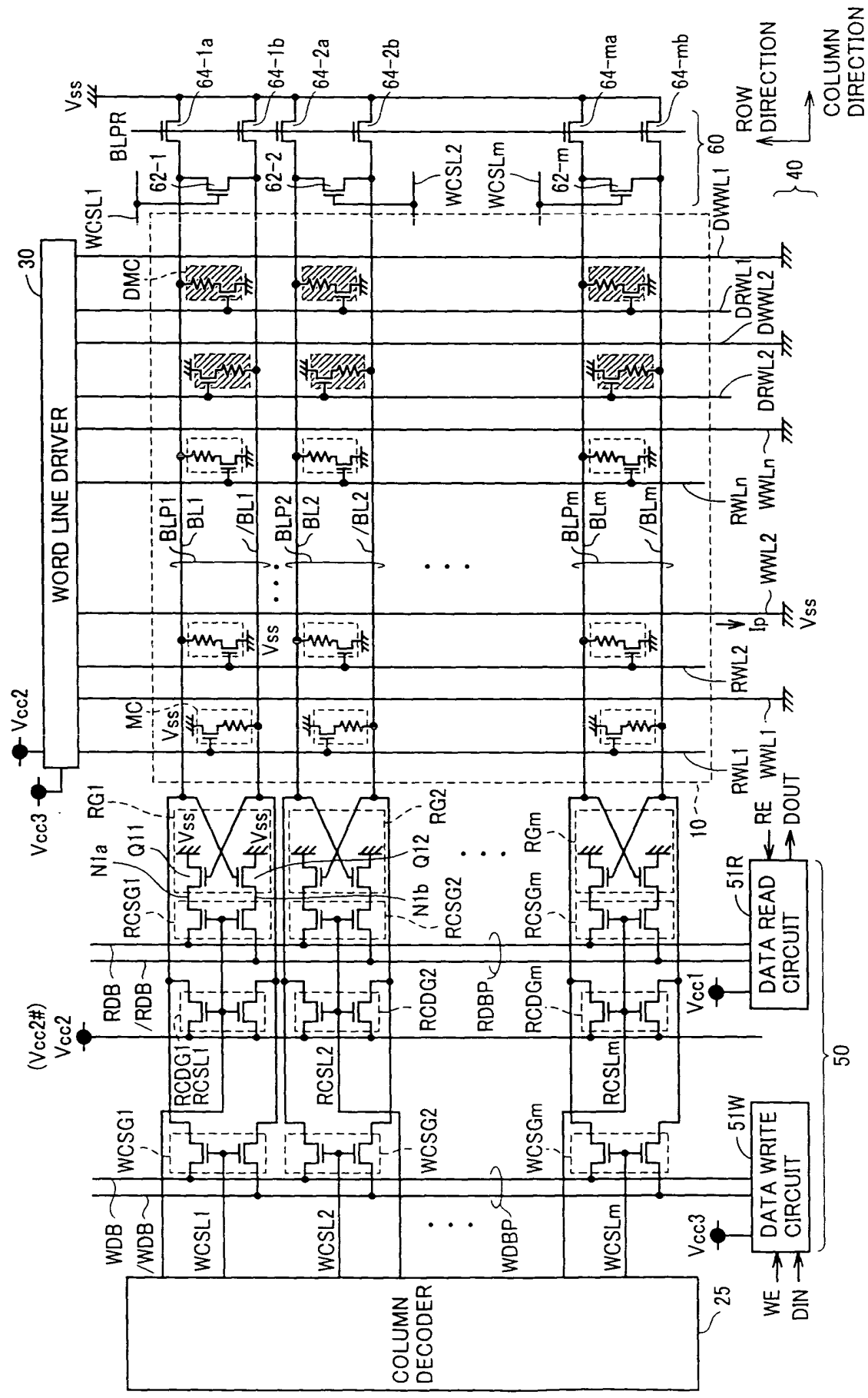


FIG.14

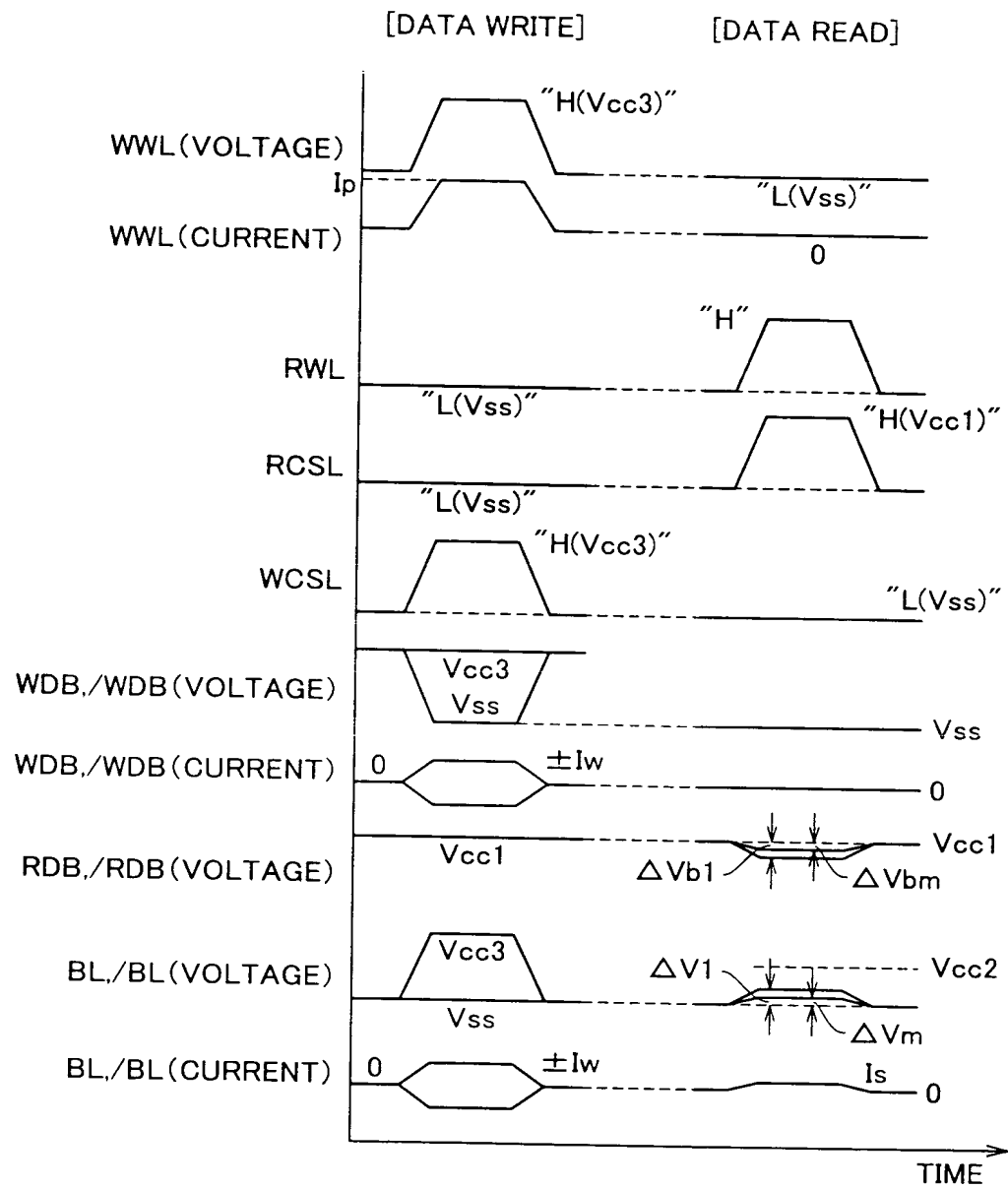


FIG.15

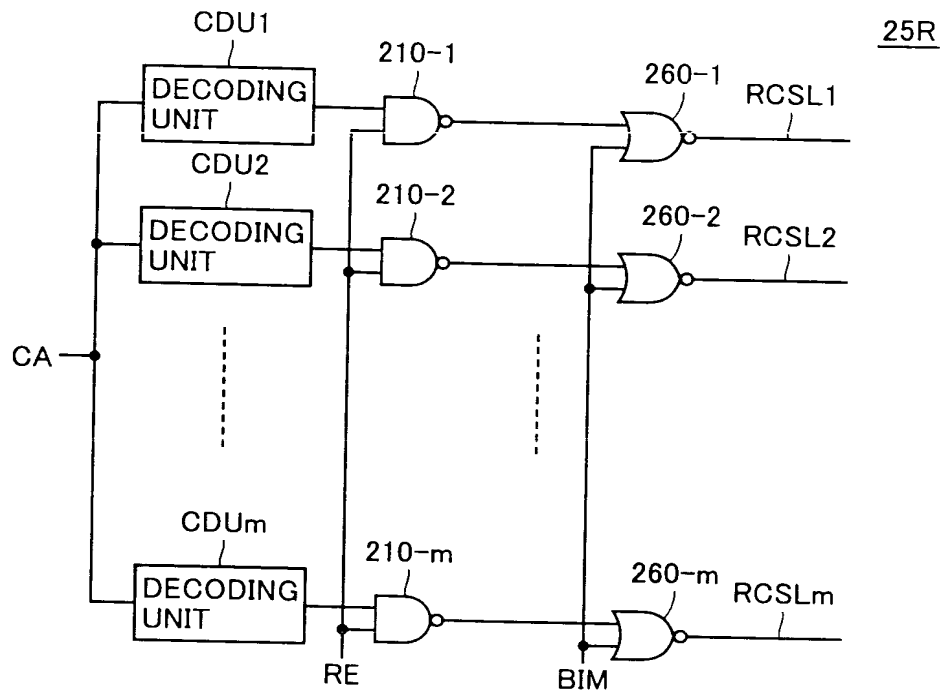


FIG.16

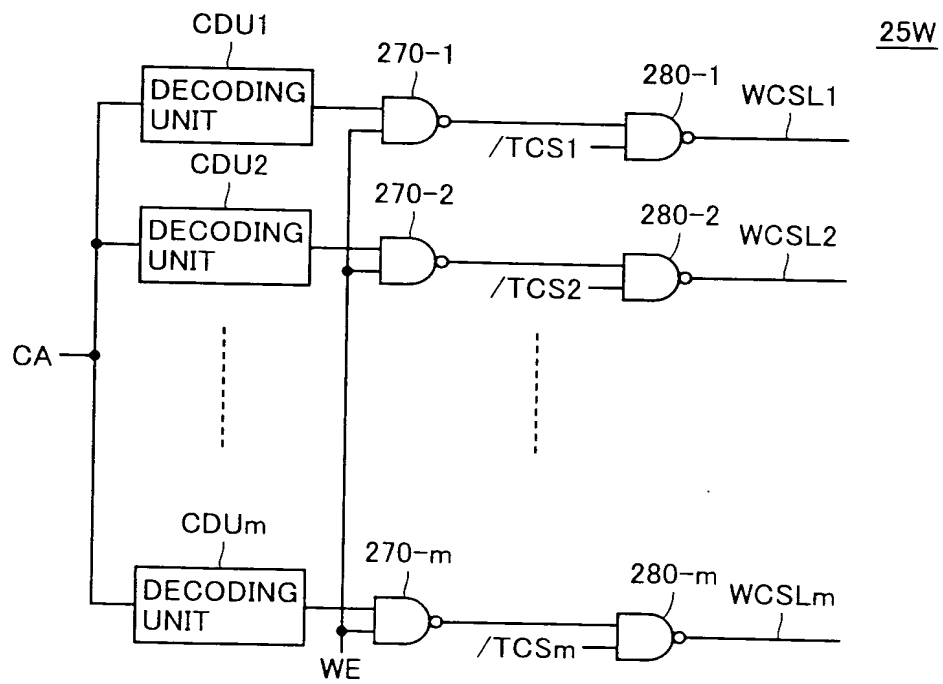
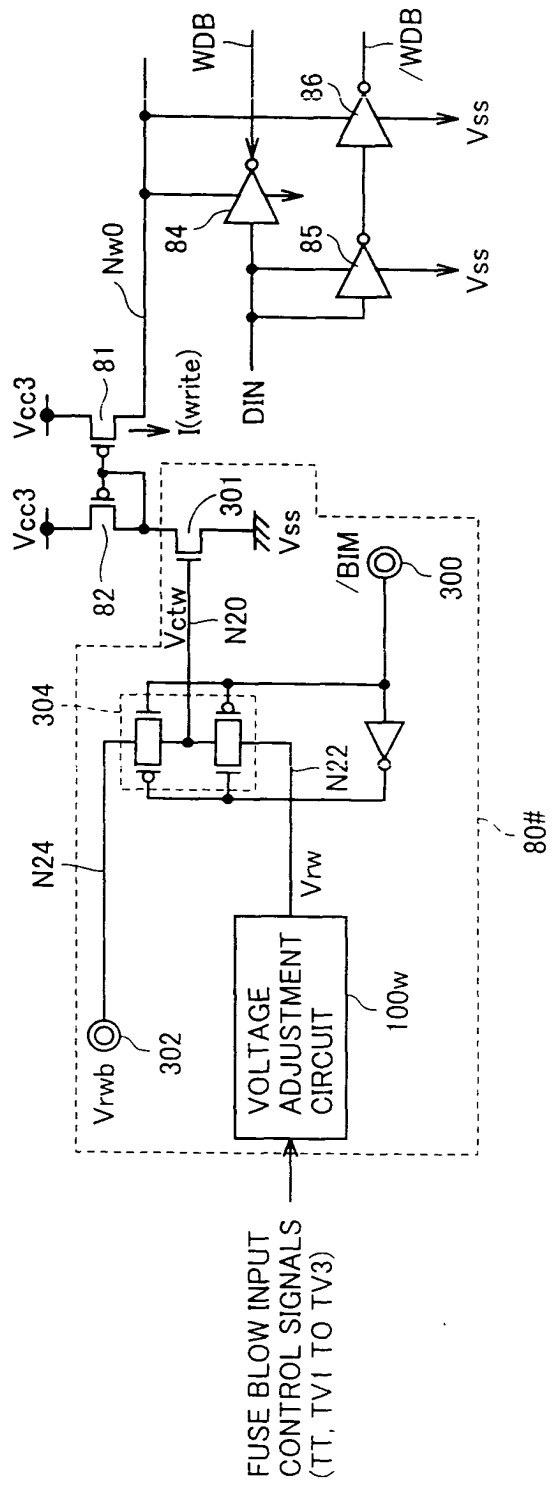


FIG.17



The diagram illustrates a memory array 30R. It features a vertical bus labeled RA on the left and a horizontal bus labeled RE at the bottom. Multiple rows of decoding units are connected to the RA bus. The first row includes a block labeled RDU1, followed by a dashed line, and then a block labeled RDU_n. Below these are blocks labeled RDU_{d1} and RDU_{d2}. Each decoding unit is connected to the RE bus through an AND gate (labeled 230-1, 230-n, 230-d1, 230-d2). The output of each AND gate is connected to an access transistor (labeled 250-1, 250-n, 250-d1, 250-d2) which is also connected to the RE bus. The other terminal of each access transistor is connected to a word line (labeled RWL1, RWL_n, DRWL1, DRWL2). A central block labeled BIM is connected to the RE bus and the word lines. A power supply Vcc1(Vcc2) is connected to the top of the array, and Vss is connected to the bottom. A dashed line indicates that the array can have more than n rows.

FIG.20

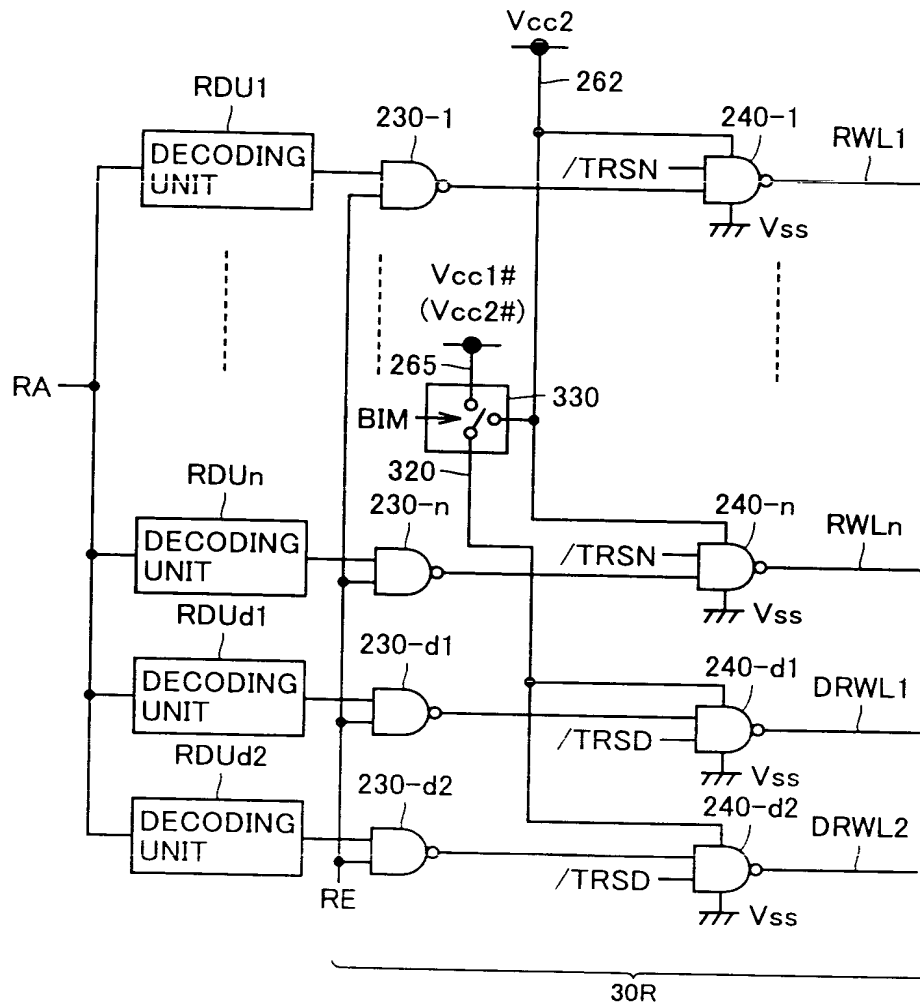


FIG.21

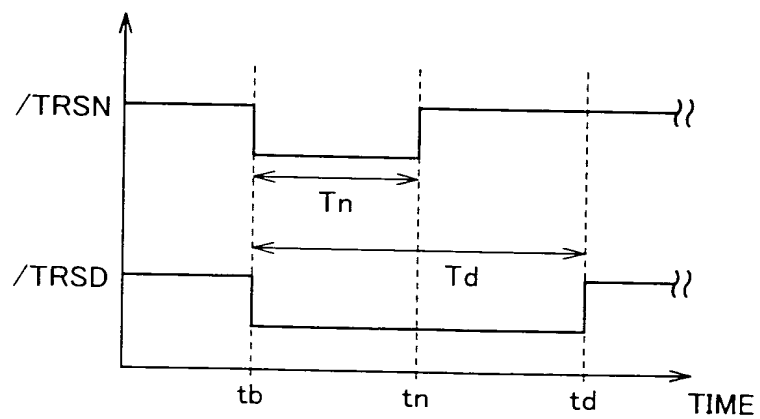


FIG.22 PRIOR ART

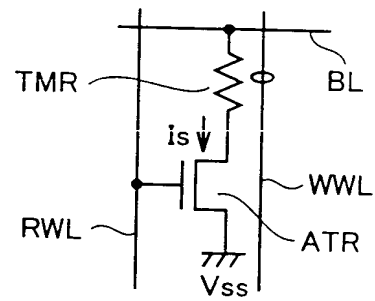


FIG.23 PRIOR ART

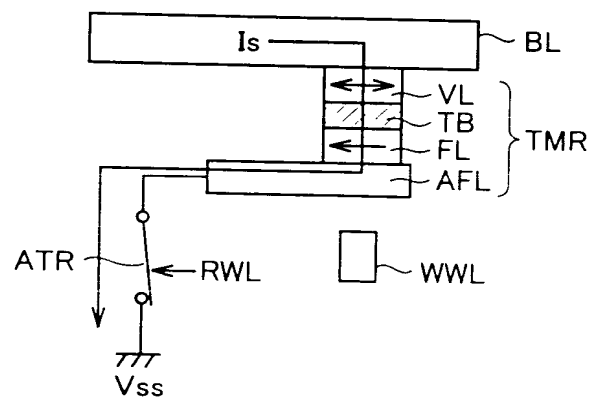


FIG.24 PRIOR ART

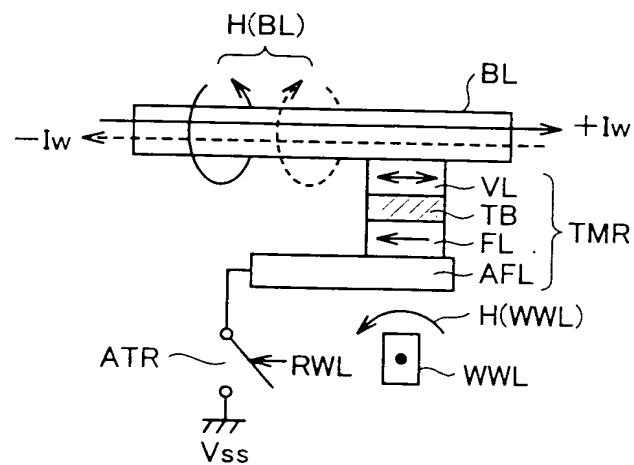


FIG.25 PRIOR ART

